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NPN Silicon Epitaxial Planar Transistor

Low frequency power amplifier application.

Power switching application.

A97<5B=75@ 85H5

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Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	35	V
V _{CE0}	Collector-Emitter Voltage	30	V
V _{EB0}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	800	mA
I _B	Base Current	160	mA
P _C	Collector Power Dissipation	200	mW
T _J , T _{stg}	Junction and Storage Temperature	-55 to +150	

F5H-B; S' 5B8' 7<5F57H9F=GH=7' 7I FJ 9G

